Smart power high-side-switch for industrial applications



Description

N channel vertical power FET with charge pump, ground referenced CMOS compatible input and diagnostic feedback, monolithically integrated with embedded protective functions.

Туре	Package	Marking
ISP752R	PG-DSO-8	1752R

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Block diagram

1 Block diagram

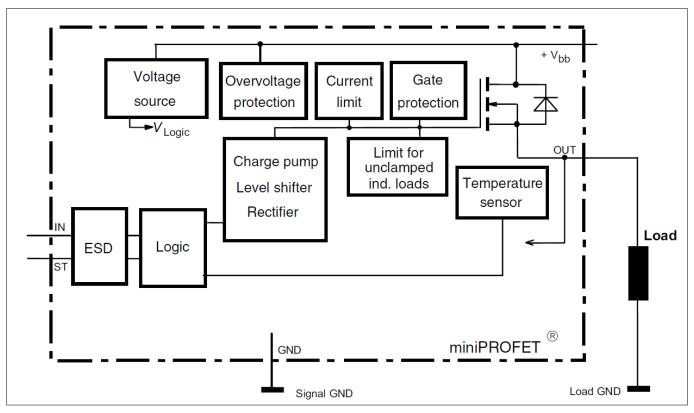


Figure 1 Block diagram



Pin configuration

2 Pin configuration

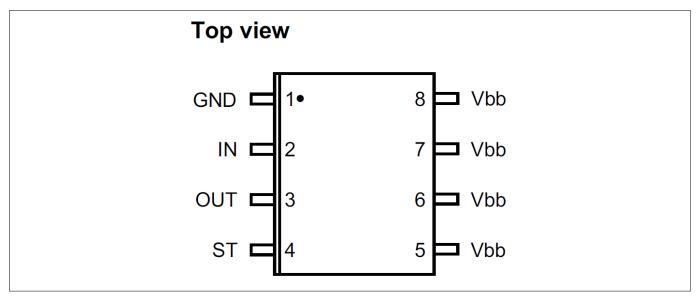


Figure 2 Pin configuration

Pin	Symbol	Function
1	GND	Logic ground
2	IN	Input, activates the power switch in case of logic high signal
3	OUT	Output to the load
4	ST	Diagnostic feedback
5	Vbb	Positive power supply voltage
6	Vbb	Positive power supply voltage
7	Vbb	Positive power supply voltage
8	Vbb	Positive power supply voltage



General product characteristics

3 General product characteristics

3.1 Absolute maximum ratings

Table 2 Maximum ratings

 $T_i = 25$ °C, unless otherwise specified

Parameter	Symbol	Value	Unit	Note or condition
Supply voltage	$V_{\rm bb}$	52	V	-
Supply voltage for full short circuit protection	V _{bb(SC)}	50	V	-
Continuous input voltage	V _{IN}	-10 to +16	V	-
Load current	I _L	self limited	А	short-circuit current, see p. 12
Current through input pin (DC)	I _{IN}	±5	mA	-
Junction temperature	Tj	150	°C	_
Operating temperature	Ta	-30 to +85	°C	_
Storage temperature	$T_{\rm stg}$	-40 to +105	°C	_
Power dissipation	P_{tot}	1.5	W	1)
Inductive load switch-off energy dissipation	E _{AS}	125	mJ	1) 2) single pulse $T_{\rm j} = 150^{\circ}{\rm C},$ $I_{\rm L} = 1~{\rm A}$ (see page 11)
Load dump protection	$V_{Loaddump}$		V	2)3)
$R_{L} = 13.5 \Omega$		73.5		$V_{\text{LoadDump}} = V_{\text{A}} +$
$R_{L} = 27 \Omega$		83.5		$V_{\rm S}$, $R_{\rm I} = 2 \Omega$, $t_{\rm d} = 400 \mathrm{ms}$, $V_{\rm IN} = \mathrm{low} \mathrm{or} \mathrm{high}$, $V_{\rm A} = 13.5 \mathrm{V}$
Electrostatic Discharge Voltage (Human Body Model)	V _{ESD}		kV	according to ANSI/ESDA/JEDEC
OUT		±6		JS001 (1.5 kΩ, 100 pF)
IN		±1		100 pr)
all other pins		±4		

Device on 50 mm \times 50 mm \times 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μ m thick) copper area for drain connection. PCB is vertical without blown air (see page 22)

² Not subject to production test, specified by design

 $V_{\rm Loaddump}$ is set up without the DUT connected to the generator per ISO 7637-1 and DIN 40839. Supply voltages higher than $V_{\rm bb(AZ)}$ require an external current limit for the GND pin, e.g. with a 150 Ω resistor in GND connection. A resistor for the protection of the input is integrated.

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General product characteristics

3.2 Thermal resistance

Table 3 Thermal resistance

Parameter	Symbol		Values			Note or condition
		Min.	Тур.	Max.		
Thermal resistance	R _{th(JA)}	_			K/W	-
minimum footprint			95	_		
6 cm ² cooling area ⁴⁾			70	83		

Device on 50 mm \times 50 mm \times 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μ m thick) copper area for drain connection. PCB is vertical without blown air (see page 22)

Smart power high-side-switch for industrial applications



Functional description and electrical characteristics

4 Functional description and electrical characteristics

4.1 Functional description

	Input level	Output level	Status
Normal operation	L	L	Н
	Н	Н	Н
Short circuit to GND	L	L	Н
	Н	L ⁵⁾	L
Short circuit to V _{bb} (in off-	L	Н	L
state)	Н	Н	Н
Overload	L	L	Н
	Н	H ⁶⁾	Н
Overtemperature	L	L	Н
	Н	L	L
Open load in off-state	L	Z ⁷⁾	H (L ⁸⁾)
	Н	Н	Н

8

Datasheet

Out = "L": V_{OUT} < 2.8 V typ.

⁶ Out = "H": $V_{OUT} > 2.8 \text{ V typ.}$

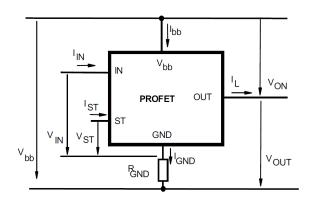
⁷ Z = high impedance, potential depends on external circuit

⁸ with external resistor between V_{bb} and OUT

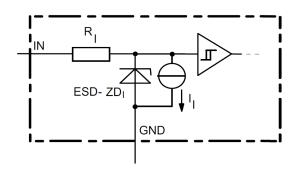


Functional description and electrical characteristics

Terms

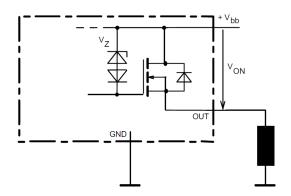


Input circuit (ESD protection)



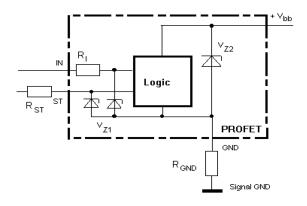
The use of ESD zener diodes as voltage clamp at DC conditions is not recommended

Inductive and overvoltage output clamp



V_{ON} clamped to 59 V min.

Overvoltage protection of logic part



$$V_{Z1} = 6.1 \text{ V typ.}, V_{Z2} = V_{bb(AZ)} = 62 \text{ V min.},$$

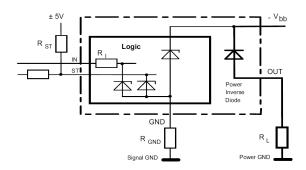
 $R_{I} = 3.5 \text{ k}\Omega \text{ typ.}, R_{GND} = 150 \Omega$

Smart power high-side-switch for industrial applications



Functional description and electrical characteristics

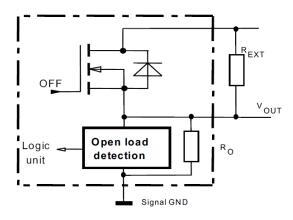
Reverse battery protection



 $R_{\text{GND}} = 150 \,\Omega$, $R_{\text{I}} = 3.5 \,\text{k}\Omega$ typ.,

Temperature protection is not active during inverse current

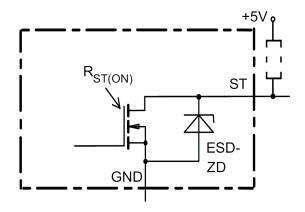
Open-load detection



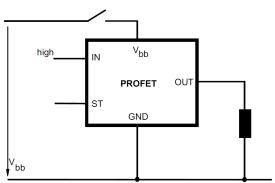
OFF-state diagnostic condition:

 $V_{OUT} > 3 \text{ V typ.}$; IN = low

Status output



$V_{ m bb}$ disconnect with charged inductive load

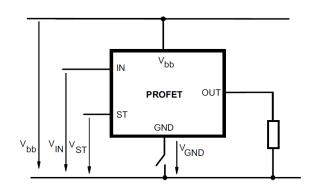


Smart power high-side-switch for industrial applications

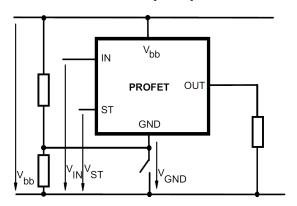


Functional description and electrical characteristics

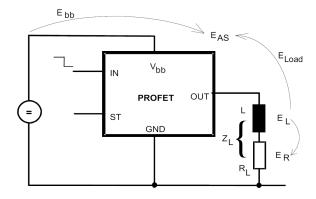
GND disconnect



GND disconnect with GND pull up



Inductive load switch-off energy dissipation



Energy stored in load inductance:

$$E_1 = 1/2 \times L \times I_1^2$$

While demagnetizing load inductance, the energy dissipated in PROFET is

$$E_{AS} = E_{bb} + E_L - E_R = V_{ON(CL)} \times I_L(t) dt$$

with an approximate solution for $R_L > 0 \Omega$:

$$E_{AS} = \frac{I_L \times L}{2 \times R_L} \times \left(V_{bb} + \left| V_{OUT(CL)} \right| \right) \times ln \left(1 + \frac{I_L \times R_L}{\left| V_{OUT(CL)} \right|} \right)$$

Smart power high-side-switch for industrial applications



Functional description and electrical characteristics

4.2 Electrical characteristics

Table 4 Electrical characteristics

at T_i = -40°C to +150°C, V_{bb} = 12 V to 42 V, unless otherwise specified

Parameter	Symbol	Values		Unit	Note or condition	
		Min.	Тур.	Max.		
Load switching capabilities and chara	acteristics					
On-state resistance	R _{ON}				mΩ	_
$T_{\rm j}$ = 25°C, $I_{\rm L}$ = 1 A, $V_{\rm bb}$ = 9 V to 52 V		_	150	200		
<i>T</i> _j = 150°C		_	270	380		
Nominal load current	I _{L(nom)}	1.3	1.7	-	A	Device on PCB ⁹⁾ $T_C = 85^{\circ}\text{C}$, $T_j \le 150^{\circ}\text{C}$
Turn-on time to 90% V _{OUT}	t _{on}	_	80	180	μs	$R_{L} = 47 \Omega$
Turn-off time to 10% V _{OUT}	$t_{ m off}$	_	80	200	μs	$R_{L} = 47 \Omega$
Slew rate on 10% to 30% V _{OUT}	dV/dt _{on}	_	0.7	2	V/µs	$R_{L} = 47 \Omega,$ $V_{bb} = 13.5 \text{ V}$
Slew rate off 70% to 40% V _{OUT}	-dV/dt _{off}	_	0.9	2	V/µs	$R_{L} = 47 \Omega,$ $V_{bb} = 13.5 \text{ V}$
Operating parameters	•		•			
Operating voltage	$V_{\rm bb(on)}$	6	_	52	V	_
Undervoltage shutoff charge pump	V _{bb(under)}				V	_
$T_{\rm j}$ = -40°C to +85°C		_	_	4		
$T_{\rm j} = 150^{\circ}{\rm C}$		_	_	5.5		
Undervoltage restart of charge pump	V _{bb(u cp)}	_	4	5.5	V	_
Standby current	I _{bb(off)}				μΑ	_
$T_{\rm j}$ = -40°C to +85°C, $V_{\rm IN}$ = low		_	_	15		
$T_{\rm j} = 150^{\circ} {\rm C}^{10}$, $V_{\rm IN} = {\rm low}$		_	_	18		
Leakage output current (included in $I_{\mathrm{bb(off)}}$)	$I_{L(off)}$	_	_	5	μΑ	$V_{IN} = low$
Operating current	I _{GND}	_	0.8	2	mA	V_{IN} = high
Protection functions 11)						
Initial peak short circuit current limit	$I_{L(SCp)}$				Α	(pin 5 to 3)
$T_{\rm j}$ = -40°C, $V_{\rm bb}$ = 20 V, $t_{\rm m}$ = 150 $\mu {\rm s}$		_	_	9		_
<i>T</i> _j = 25°C		_	6.5	_		_

Device on 50 mm × 50 mm × 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air (see page 22)

Datasheet 12 Rev. 1.2

¹⁰ Higher current due temperature sensor

Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

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Functional description and electrical characteristics

Table 4 Electrical characteristics (continued)

at T_i = -40°C to +150°C, V_{bb} = 12 V to 42 V, unless otherwise specified

Parameter	Symbol		Values			Note or condition
		Min.	Тур.	Max.		
$T_{\rm j} = 150^{\circ}{\rm C}$		4	_	_		-
$T_{\rm j}$ = -40°C to +150°C, $V_{\rm bb}$ > 40 V (see p. 17)		_	5 ¹²⁾	_		-
Repetitive short circuit current limit, $T_j = T_{jt}$	I _{L(SCr)}				A	(see Timing diagrams)
<i>V</i> _{bb} < 40 V		-	6	-		
V _{bb} > 40 V		-	4.5	_		
Output clamp (inductive load switch off)	V _{ON(CL)}	59	63	-	V	$V_{\text{OUT}} = V_{\text{bb}} - V_{\text{ON(CL)}},$ $I_{\text{bb}} = 4 \text{ mA}$
Overvoltage protection	V _{bb(AZ)}	62	-	_	V	$I_{bb} = 4 \text{ mA}$
Thermal overload trip temperature	$T_{\rm jt}$	150	_	_	°C	_
Thermal hysteresis	ΔT _{jt}	_	10	_	K	_
Reverse battery	-	<u>'</u>			1	
Reverse battery	-V _{bb}	_	_	52	V	14)
Drain-source diode voltage $(V_{OUT} > V_{bb})$	-V _{ON}	_	600	_	mV	<i>T</i> _j = 150°C
Input and status feedback						
Input turn-on threshold voltage	$V_{IN(T+)}$	_	_	2.2	V	_
Input turn-off threshold voltage	V _{IN(T-)}	0.8	_	_	V	_
Input threshold hysteresis	$\Delta V_{\rm IN(T)}$	_	0.4	_	V	_
Off state input current $V_{IN} = 0.7 \text{ V}$	I _{IN(off)}	1	-	25	μΑ	-
On state input current	I _{IN(on)}	3	_	25	μΑ	V _{IN} = 5 V
Status output (open drain), Zener limit voltage	V _{ST(high)}	5.4	6.1	-	V	I _{ST} = 1.6 mA
Status output (open drain), ST low voltage	V _{ST(low)}				V	-
$T_{\rm j}$ = -40°C to +25°C, $I_{\rm ST}$ = 1.6 mA		_	_	0.4		
$T_{\rm j}$ = 150°C, $I_{\rm ST}$ = 1.6 mA		_	_	0.6		
Status invalid after positive input slope	$t_{d(ST+)}$	_	120	160	μs	15)

Not subject to production test, specified by design

see also $V_{ON(CL)}$ in circuit diagram on page 9

Requires a $150\,\Omega$ resistor in GND connection. The reverse load current through the intrinsic drain-source diode has to be limited by the connected load. Power dissipation is higher compared to normal operating conditions due to the voltage drop across the drain-source diode. The temperature protection is not active

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Functional description and electrical characteristics

Table 4 Electrical characteristics (continued)

at T_i = -40°C to +150°C, V_{bb} = 12 V to 42 V, unless otherwise specified

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Тур.	Max.		
						V _{bb} = 20 V
Status invalid after negative input slope ¹⁵⁾	$t_{d(ST-)}$	-	250	400	μs	-
Input resistance	R _I	2	3.5	5	kΩ	see page 9
Diagnostic characteristics						
Short circuit detection voltage	V _{OUT(SC)}	_	2.8	_	V	_
Open load detection voltage	V _{OUT(OL)}	_	3	4	V	16)
Internal output pull down	R _O	_	200	_	kΩ	17)
						$V_{\text{OUT(OL)}} = 4 \text{ V}$ (see page 10 and page 19)

during reverse current operation! Input current has to be limited (see *Absolute maximum ratings* on page 6).

No delay time after overtemperature switch off and short circuit in on-state

¹⁶ External pull up resistor required for open load detection in off state

Not subject to production test, specified by design

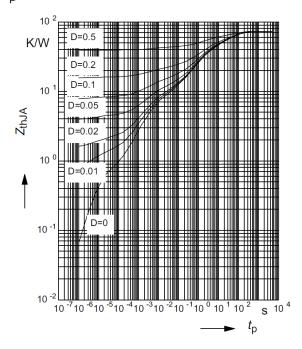


Functional description and electrical characteristics

4.3 Typical performance characteristics

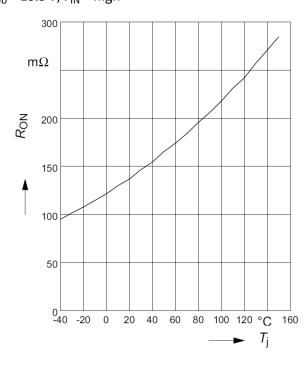
Typ. transient thermal impedance $Z_{thJA} = f(t_p)$ @ 6 cm² heatsink area

 $D = t_{\rm D}/T$



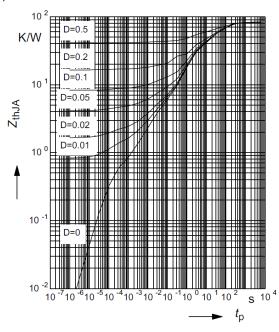
Typ. on-state resistance $R_{ON} = f(T_j)$

$$V_{\rm bb}$$
 = 13.5 V; $V_{\rm IN}$ = high



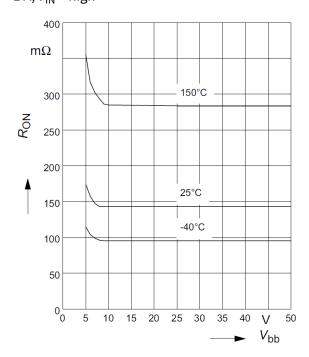
Typ. transient thermal impedance $Z_{\text{thJA}} = f(t_p)$ @ minimum footprint

$$D = t_p/T$$



Typ. on-state resistance $R_{ON} = f(V_{bb})$

$$I_L = 1 \text{ A}$$
; $V_{IN} = \text{high}$



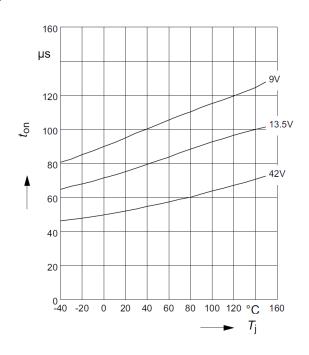
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infineon

Functional description and electrical characteristics

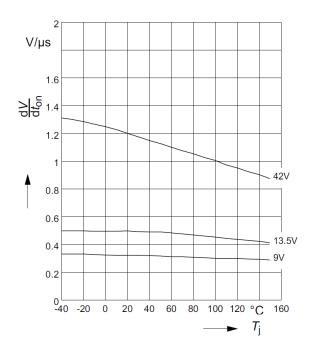
Typ. turn-on time $t_{on} = f(T_i)$

 $R_L = 47 \Omega$



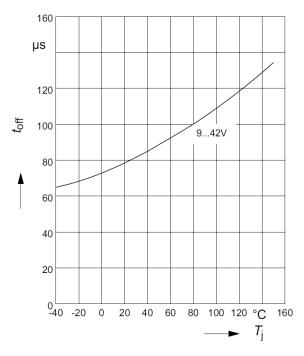
Typ. slew rate on $dV/dt_{on} = f(T_j)$

 $R_L = 47 \Omega$



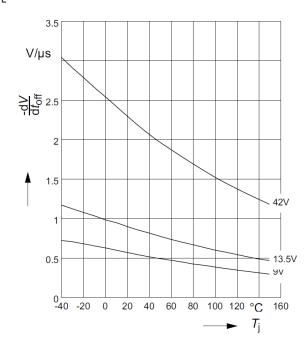
Typ. turn-off time $t_{off} = f(T_i)$

 $R_L = 47 \Omega$



Typ. slew rate off $dV/dt_{off} = f(T_i)$

 $R_L = 47 \Omega$



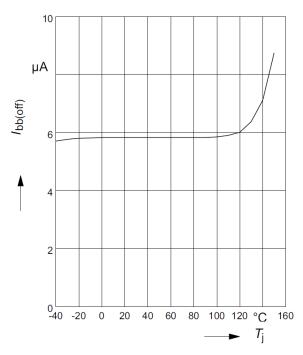
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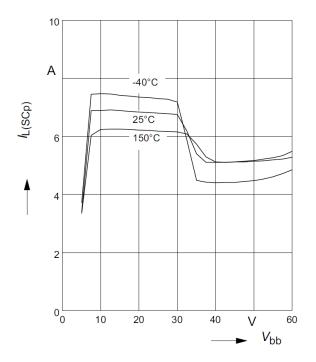
Functional description and electrical characteristics

Typ. standby current $I_{bb(off)} = f(T_i)$

$$V_{\rm bb}$$
 = 42 V; $V_{\rm IN}$ = low

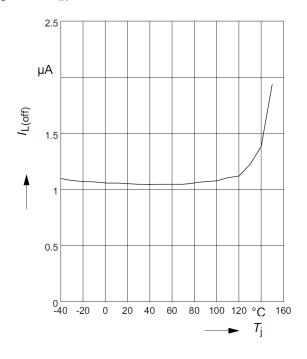


Typ. initial peak short circuit current limit $I_{L(SCp)} = f(V_{bb})$



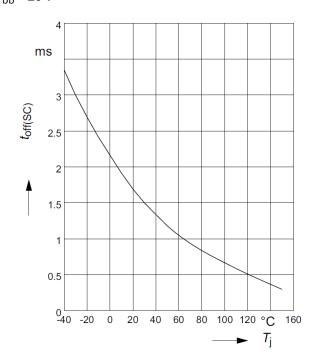
Typ. leakage current $I_{L(off)} = f(T_j)$

$$V_{\rm bb}$$
 = 42 V; $V_{\rm IN}$ = low



Typ. initial short circuit shutdown time $t_{\text{off(SC)}} = f(T_{j, \text{start}})$

$$V_{\rm bb} = 20 \, \rm V$$



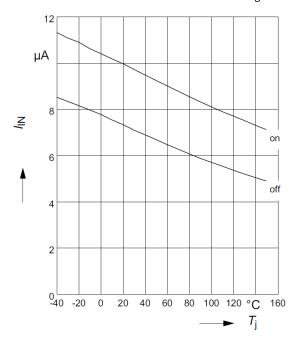
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Functional description and electrical characteristics

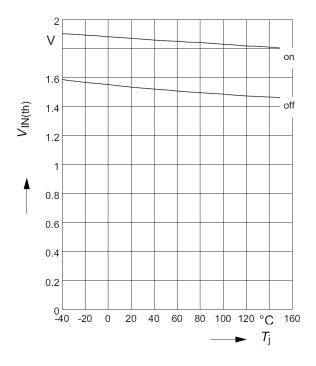
Typ. input current $I_{IN(on/off)} = f(T_j)$

 $V_{\rm bb}$ = 13.5 V; $V_{\rm IN}$ = low/high; $V_{\rm INlow} \le 0.7$ V; $V_{\rm INhigh}$ = 5 V



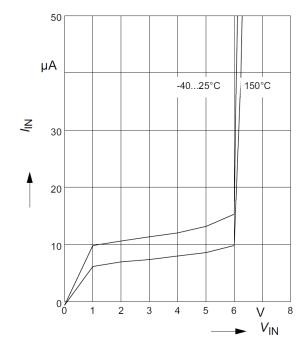
Typ. input threshold voltage $V_{IN(th)} = f(T_j)$

 $V_{\rm bb} = 13.5 \, \rm V$



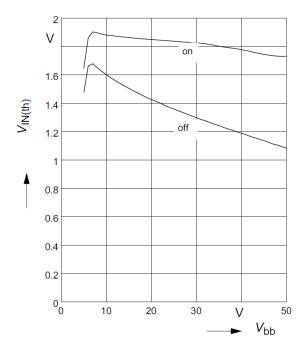
Typ. input current $I_{IN} = f(V_{IN})$

 $V_{\rm bb}$ = 13.5 V



Typ. input threshold voltage $V_{IN(th)} = f(V_{bb})$

 $T_{i} = 25^{\circ}C$



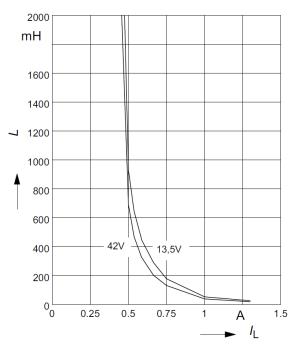
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Functional description and electrical characteristics

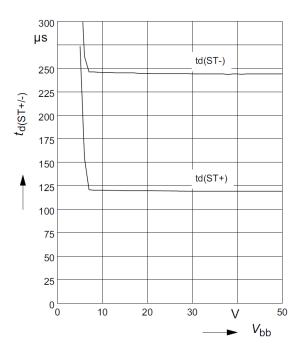
Maximum allowable load inductance for a single switch off $L = f(I_L)$

 $T_{\text{jstart}} = 150^{\circ}\text{C}, R_{\text{L}} = 0 \Omega$



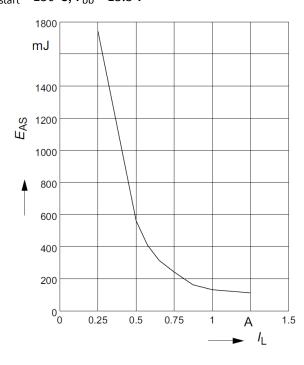
Typ. status delay time $t_{d(ST)} = f(V_{bb})$

$$T_i = 25$$
°C

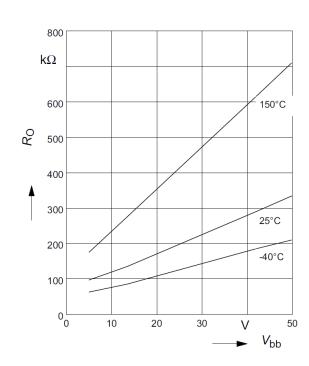


Maximum allowable inductive switch-off energy, single pulse $E_{AS} = f(I_L)$

 $T_{\rm jstart} = 150^{\circ} \text{C}, V_{\rm bb} = 13.5 \text{ V}$



Typ. internal output pull down $R_0 = f(V_{bb})$



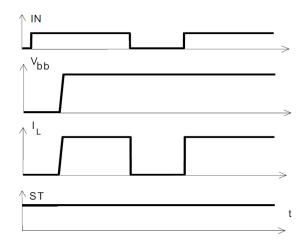
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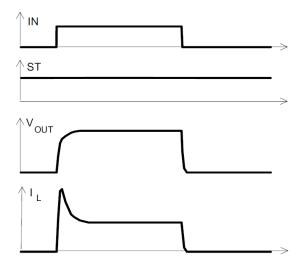
Functional description and electrical characteristics

4.4 Timing diagrams

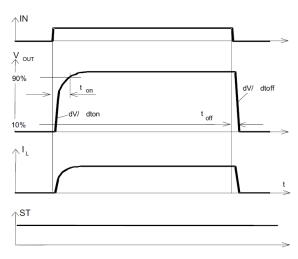
$V_{\rm bb}$ turn on



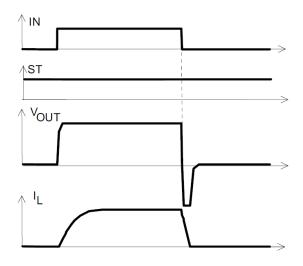
Switching a lamp



Switching a resistive load, turn-on/off time and slew rate definition



Switching an inductive load

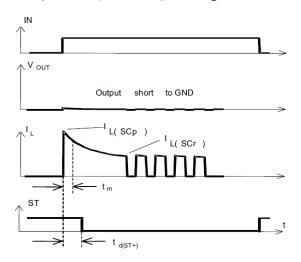


Smart power high-side-switch for industrial applications



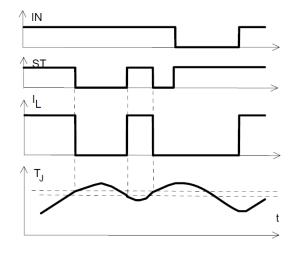
Functional description and electrical characteristics

Turn on into short circuit, shut down by overtemperature, restart by cooling

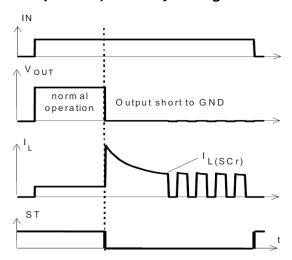


Heating up of the chip may require several milliseconds, depending on external conditions.

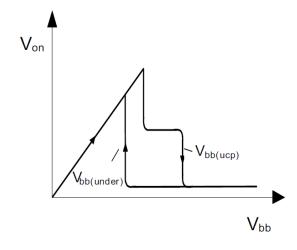
Overtemperature: Reset if $T_i < T_{it}$



Short circuit in on-state shut down by overtemperature, restart by cooling



Undervoltage restart of charge pump





Package information

5 Package information

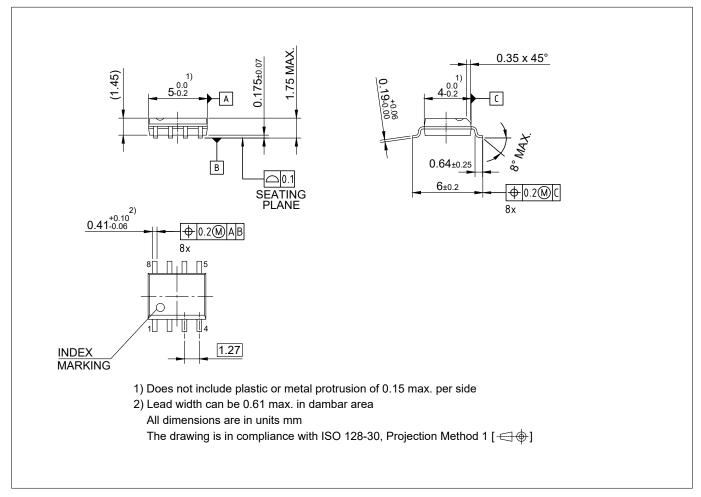


Figure 3 PG-DSO-8

Green Product (RoHS compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (Pbfree finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

Information on alternative packages

Please visit www.infineon.com/packages.

Smart power high-side-switch for industrial applications



Revision history

6 Revision history

Document version	Date of release	Description of changes				
1.2	2019-07-25	Datasheet updated: ESD ratings for HBM updated according to ANSI/ESDA/JEDEC JS001 Editorial changes				
1.1	2008-09-26	All pages: • Added new Infineon logo • Initial version of RoHS-compliant derivate of the ISP752R Page 1 and 17: • Added RoHS compliance statement and Green product feature • Package changed to RoHS compliant version Page 18: Added Revision history Page 19: Update of disclaimer				

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 ${\bf Email: erratum@infineon.com}$

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